

**INTEGRATED CIRCUIT FIELD EFFECT TRANSISTORS INCLUDING
CHANNEL-CONTAINING FIN HAVING REGIONS OF HIGH AND LOW
DOPING CONCENTRATIONS AND METHODS OF FABRICATING SAME**

Abstract of the Disclosure

Integrated circuit field effect transistors include an integrated circuit substrate and a fin that projects away from the integrated circuit substrate, extends along the integrated circuit substrate, and includes a top that is remote from the integrated
5 circuit substrate. A channel region is provided in the fin that is doped a conductivity type and has a higher doping concentration of the conductivity type adjacent the top than remote from the top. A source region and a drain region are provided in the fin on opposite sides of the channel region, and an insulated gate electrode extends across the fin adjacent the channel region. Related fabrication methods also are described